

# ABSTRACT

A base polymer having incorporated an ester group  
5 having a fluorinated alicyclic unit is provided. A resist  
composition comprising the polymer is sensitive to high-  
energy radiation, and has excellent sensitivity at a  
wavelength of less than 200 nm, significantly improved  
transparency by virtue of the fluorinated alicyclic units  
10 incorporated as well as satisfactory plasma etching  
resistance. The resist composition has a low absorption at  
the exposure wavelength of a F<sub>2</sub> laser and is ideal as a  
micropatterning material in VLSI fabrication.